

## GenX3<sup>™</sup> 300V IGBT

## T IXGH60N30C3

# High Speed IGBTs for 50-150kHz switching



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G = Gate E = Emitter

#### Features

- High Frequency IGBT
- Square RBSOA
- High avalanche capability
- Drive simplicity with MOS Gate Turn-On
- High current handling capability

#### Applications

- PFC Circuits
- PDP Systems
- Switched-mode and resonant-mode converters and inverters
- SMPS
- AC motor speed control
- DC servo and robot drives
- DC choppers

Symbol	Test Conditions	Maximum Ratings			
V <sub>CES</sub>	$T_{J} = 25^{\circ}C \text{ to } 150^{\circ}C$	300 \			
V <sub>CGR</sub>	$T_{J} = 25^{\circ}C$ to 150°C, $R_{GE} = 1M\Omega$	300	V		
$V_{ges}$	Continuous	±20	V		
V <sub>gem</sub>	Transient	±30	V		
I <sub>C25</sub>	$T_c = 25^{\circ}C$ (Limited by leads)	75	А		
I <sub>C110</sub>	$T_{c} = 110^{\circ}C$ (chip capability)	60	А		
см	$T_c = 25^{\circ}C$ , 1ms	420	A		
I <sub>A</sub>	$T_c = 25^{\circ}C$	60	А		
E <sub>AS</sub>	$T_c = 25^{\circ}C$	400	mJ		
SSOA (RBSOA)	$V_{_{GE}}$ = 15V, T <sub>VJ</sub> = 125°C, R <sub>G</sub> = 5 $\Omega$ Clamped inductive load @ $\leq$ 300V	I <sub>CM</sub> = 170	А		
P <sub>c</sub>	$T_c = 25^{\circ}C$	300	W		
T		-55 +150	°C		
T <sub>JM</sub>		150	°C		
T <sub>stg</sub>		-55 +150	°C		
T <sub>l</sub> T <sub>sold</sub>	Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10s	300 260	°C ℃		
M <sub>d</sub>	Mounting torque (TO-247)	1.13/10	Nm/lb.in.		
Weight		6	g		

Symbol	Test Conditions	Characteristic V (T <sub>J</sub> = 25°C, unless otherwise spec Min.   Typ.   Max.					
BV <sub>CES</sub> V <sub>GE(th)</sub>	$\begin{array}{ll} I_{c} &= 250 \mu A,  V_{GE} = 0 V \\ I_{c} &= 250 \mu A,  V_{CE} = V_{GE} \end{array}$	300 2.5		5.0	V V		
I <sub>ces</sub>	$V_{CE} = V_{CES}$ $V_{GE} = 0V$	T <sub>J</sub> = 125°C		30 750	μΑ μΑ		
I <sub>ges</sub>	$V_{_{CE}}$ = 0V, $V_{_{GE}}$ = ± 20V			±100	nA		
V <sub>CE(sat)</sub>	I <sub>c</sub> = 60A, V <sub>GE</sub> = 15V	T <sub>J</sub> = 125°C	1.55 1.60	1.8	V V		

C = Collector TAB = Collector

#### Symbol **Test Conditions Characteristic Values** $(T_1 = 25^{\circ}C, unless otherwise specified)$ Min. Typ. $I_{c} = 0.5 \bullet I_{c110}, V_{cE} = 10V$ 28 46 $\mathbf{g}_{\mathrm{fs}}$ Pulse test, $t \le 300 \mu s$ ; duty cycle, $d \le 2\%$ . C 3800 $V_{ce} = 25V, V_{ge} = 0V, f = 1MHz$ 240 C<sub>oes</sub> C 63 $\mathbf{Q}_{g}$ 101 $I_{c} = I_{c110}, V_{ge} = 15V, V_{ce} = 0.5 \bullet V_{ces}$ $\mathbf{Q}_{\mathrm{ge}}$ 21 $\mathbf{Q}_{\mathrm{gc}}$ 37 23 t<sub>d(on)</sub> Inductive Load, T<sub>1</sub> = 25°C 28 t<sub>ri</sub> $I_{\rm C} = 0.5 \bullet I_{\rm C110}, V_{\rm GE} = 15V$ $\boldsymbol{\mathsf{E}}_{\mathrm{on}}$ 0.15 $V_{_{CE}}$ = 200V, $R_{_{G}}$ = 5 $\Omega$ 108 t<sub>d(off)</sub> 68 t<sub>fi</sub> E<sub>off</sub> 0.30 22 t<sub>d(on)</sub> 28 t

Inductive Load, T<sub>1</sub> = 125°C

 $I_{\rm C} = 0.5 \bullet I_{\rm C110}, V_{\rm GE} = 15V$ 

 $V_{ce} = 200V, R_g = 5\Omega$ 

E<sub>on</sub>

 $\mathbf{t}_{d(off)}$ 

R<sub>thJC</sub> R<sub>thCK</sub>

t<sub>fi</sub> E\_\_\_\_

### IXGH60N30C3



Max.

S

pF

pF

pF

nC

nC

nC

ns

ns

mJ

ns

ns

mJ

ns

ns

mJ

ns

ns

mJ

°C/W

0.42 °C/W

160

0.55

0.26

120

101

0.40

0.21

А	4.7	5.3	.185	.209
A <sub>1</sub>	2.2	2.54	.087	.102
A <sub>2</sub>	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b,	1.65	2.13	.065	.084
b <sub>2</sub>	2.87	3.12	.113	.123
С	.4	.8	.016	.031
D	20.80	21.46	.819	.845
Е	15.75	16.26	.610	.640
е	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	242	BSC

#### **ADVANCE TECHNICAL INFORMATION**

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

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IXYS MOSFETs and IGBTs are covered	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
by one or moreof the following U.S. patents:	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	



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